

2019 Conference on Lasers and Electro-Optics Europe & European Quantum Electronics Conference

Advance Programme

Munich ICM

International Congress Centre Munich, Germany 23 - 27 June 2019

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Hall B0

Mode-Locked States in Semiconductor Lasers Symmetry Properties and Coexistence of the

sia; ²Centre de Nanosciences et de Nanotechnologies ·A. V. Kovalev¹, K. Merghem², A. Ramdane², and E.A. Palaiseau, France Viktorov'; 'ITMO University, Saint Petersburg, Rus-

which possess different repetition rates and temporal ing of translationally symmetrical mode-locked regimes and demonstrate coexistence, multistability and switchpuise profiles. metry properties of mode-locked semiconductor lasers We, experimentally and numerically, explore the sym-

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Superradiance as a Way to the Steady-State Multimode and Ultrashort Pulsed Lasing in CW Quantum-Dot Heterolasers

A&M University, College Station, USA Russia; ²Department of Physics and Astronomy, Texas Physics, Russian Academy of Science, Nizhny Novgorod, Kocharovskaya¹, and A. Seleznev¹; ¹Institute of Applied ·V. Kocharovsky¹, A. Mishin¹, V. Kocharovsky^{1,2}, E.

short pulses and support many steady-state modes which few superradiant modes will emit the sequences of ultrathe superradiance under CW pumping and show that a We design the pulsed quantum-dot heterolaser based on

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laser monolithically grown on germanium Y. Zhou^{1,2}, J. Duan², H. Huano², C. Coo³ Self-sustained pulse oscillations in a quantum dot

Y. Zhou'.', J. Duan², H. Huang², C. Cao³, Q. Gong³, F. Grillot^{2,4}, and •C. Wang¹; ShanghaiTech Univer-sity, Shanghai, China; ²Telecom ParisTech, Paris, France; Technology, Shanghai, China; ⁴University of New-Mexico Shanghai Institute of Microsystem and Information

sustained pulse oscillations with one, two, and three periods at different pump currents, without incorporating laser monolithically grown on germanium exhibits self We show that a free-running InAs/GaAs quantum dot

Repetition rate locking of mutually injected monolithic passively mode-locked semiconductor quantum dot lasers

> cational Institute of Sterea Ellada, Department of Elec-Engineering, 12243 Athens, Greece; ³Technological Eduof West Attica, Department of Electrical and Electronics Applied Physics, 64289 Darmstadt, Germany; ²University •C. Weber¹, D. Auth¹, I. Simos², C. Simos³, and S. Breuer¹; ¹Technische Universität Darmstadt, Institute of tronic Engineering, 35100 Lamia, Greece

strated and theoretically explained for varying delay tor lasers emitting at 1250 nm is experimentally demonlength and biasing conditions. mode-locked InAs/InGaAs-quantum-dot semiconductwo mutually injected monolithic two-section passively Repetition rate and emission wavelength locking of

gain-switched semiconductor lasers Analysis of optical frequency comb generation in

E.T.S.1 Telecomunicación, Universidad Politécnica de Madrid, Madrid, Spain; ²Instituto de Física de Cantabria (CSIC-Universidad de Cantabria), Santander, Spain A. Rosado[†], A. Pérez-Serrano[†], J.M. García Tijero[†], A Valle', L. Pesquera', and I. Esquivias'; 'CEMDATIC-

best driving conditions for specific comb characteristics generation of OFCs from gain-switched semiconductor lasers. The results provide an excellent guide to select the We have analysed experimentally and by simulations the

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Feedback Interferometry Quasi-Linear Displacement Measurement with Laser

France; 'ITMO University, Saint Petersburg, Russia A. Locquet¹; ¹UMI 2958 Georgia Tech-CNRS, Metz, D. Choil, M.J. Wishonl, E.A. Viktorov2, D.S. Citrinl, and

any post-processing, to a minimal detectible displaceback interferometry setup, that leads, in the absence of making use of the traditional, unmodified, laser feed-We demonstrate experimentally a displacement sensor, ment as small as 12 nm.

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regardless of types of fiber dispersions Pulse compression using chirp of transistor lasers

Center for Applied Sciences, Academia Sinica, Taipei Taiwan (R.O.C.); ³Graduate Institute of Photonics and wan University, Taipei, Taiwan (R.O.C.); ²Research Department of Electrical Engineering, National Tai-C.-T. Tung', S.-W. Chang', and •C.-H. Wul.3 National Taiwan University, Taipei

Taiwan (R.O.C.)

compressed in both normal and abnormal dispersion. fibers. It shows that the pre-chirped pulse of TLs can be lasers and the reshape of the optical Gaussian pulse in We demonstrate the small-signal chirping of transistor

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mode-locked lasers with V-shaped cavity geometry •J. Hausen, S. Meinecke, and K. Lüdge; Institute of Theo Tailoring localization features in passively

multi-stability of the off-solution and the periodic mode cavity geometry on localized structures, forming from a of a passively mode-locked laser with V-shaped external We examine the influence of the distinct cavity features retical Physics, TU Berlin, Berlin, Germany

B.-B. Zhao and •C. Wang; ShanghaiTech University, Quantum Cascade Lasers Subject to Optical Injection **Optical Frequency Comb Generation Using**

tunable via fine control of injection ratio and/or detunto optical injection. The comb frequency is continuously period-one dynamics of quantum cascade lasers subject We propose to produce optical frequency combs using

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The contribution has been withdrawn

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Relative Intensity Noise of 3.4 μ m Interband Cascade

haiTech University, Shanghai, China Deng, Y.-T. Gu, B.-B. Zhao, and •C. Wang; Shang-

operated at room temperature of a continuous-wave In As/GaS We experimentally show that the relative intensity noise low as -130 ascade laser

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cascade laser frequency combs Modelling the spatio-temporal dynamics of quantum

of Solid State Electronics, TU Wien, Vienna, Austria; •N. Opačak¹, G. Strasser^{1,2}, and B. Schwarz¹; ¹Institute enna, Austria *Center for Micro- and Nanostructures, TU Wien, Vi

> inclusion of optical non-linearities and group velocity namics of the QCL phase-locking process through the A theoretical model which describes the intra-cavity dy recent experimental results dispersion is presented. The del is found to agree with

mid-infrared ring quantum cascade lasers High frequency modulation characteristics of

gies and Analytics, Technische Universität Wien, Vienna dad Carlos III de Madrid, Madrid, Spain Austria; ³Electronics Technology Department, University •B. Hinkov¹, J. Hayden², R. Szedlak¹, F. Pilat¹, P. Martin, Mateos³, B. Jerez³, P. Acedo³, G. Strasser¹, and B. Lend², Wien, Vienna, Austria; 'Institute of Chemical Technolo Institute of Solid State Electronics, Technische Universitä

data transfer applications. They are investigated and compared to identical Fahrm normal properties. QCLs up to 800 MHz, designed for spectroscopic compared to identical Fabry-Pérot devices band characteristics of mid-infrared emitting ring-DIB We show the high frequency modulation and single side

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Coupled Phase-Locked Array of Quantum Cascade Above-Threshold Modeling of Resonant Leaky-Wate

L.l. Mawst², and A. Belyanin⁴; ¹SRC RF TRINIT, Troitsk, Russia; ²University of Wisconsin-Madison, Mad-son, USA; ³Intraband, LLC, Madison, USA; ⁴Texas A&N N.N. Elkin¹, A.P. Napartovich¹, D.V. Vysotsky¹, C. Sigler², C. Boyle², J.D. Kirch², T. Earles³, D. Botz¹ University, College Station, USA

Phase locked quantum cascade laser array emitting a the power of its single mode CW operation show how theoretical model reveals the factors limiting $4.7 \mu m$ is an efficient source of high quality radiation.

CB-P.58 MON

Y. Deng and . C. Wang: Shanghai Tech University, Shang-Rate Equation Modeling of Interband Cascade Lases

relative intensity noise, and the phase noise. lasers, and theoretically demonstrate that a small We propose a rate equation model for interband cascade stage number reduces the modulation bandwidth, gain gain

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